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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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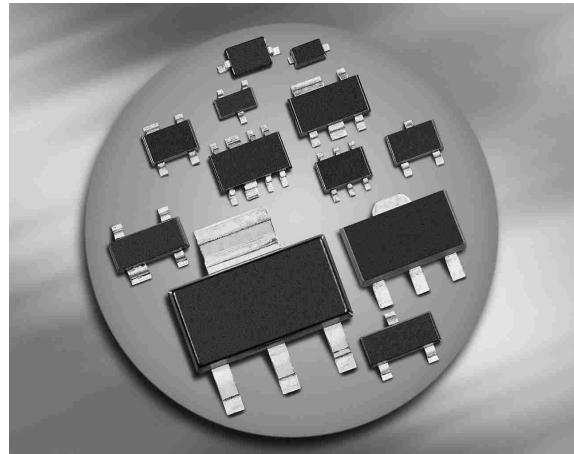
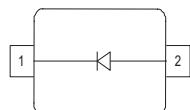
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Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

Silicon PIN Diode

- Optimized for low current antenna switches in hand held applications
- Very low forward resistance (typ. 1.5Ω @ $I_F = 1 \text{ mA}$)
- Low capacitance at zero volt reverse bias at frequencies above 1 GHz (typ. 0.28 pF)
- Very low signal distortion
- Pb-free (RoHS compliant) package


BAR88-02LRH
BAR88-02V


Type	Package	Configuration	$L_S(\text{nH})$	Marking
BAR88-02LRH	TSLP-2-7	single, leadless	0.4	U8
BAR88-02V	SC79	single	0.6	U

Maximum Ratings at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	80	V
Forward current	I_F	100	mA
Total power dissipation BAR88-02LRH $T_s \leq 133^\circ\text{C}$	P_{tot}	250	mW
BAR88-02V, $T_s \leq 123^\circ\text{C}$		250	
Junction temperature	T_j	150	$^\circ\text{C}$
Operating temperature range	T_{op}	-55 ... 125	
Storage temperature	T_{stg}	-55 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾ BAR88-02LRH	R_{thJS}	≤ 65	K/W
BAR88-02V		≤ 105	

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

DC Characteristics

Breakdown voltage $I_{(BR)} = 5 \mu\text{A}$	$V_{(BR)}$	80	-	-	V
Reverse current $V_R = 60 \text{ V}$	I_R	-	-	50	nA
Forward voltage $I_F = 1 \text{ mA}$	V_F	-	0.75	0.9	V
$I_F = 100 \text{ mA}$		-	0.95	1.2	

¹⁾For calculation of R_{thJA} please refer to Application Note Thermal Resistance

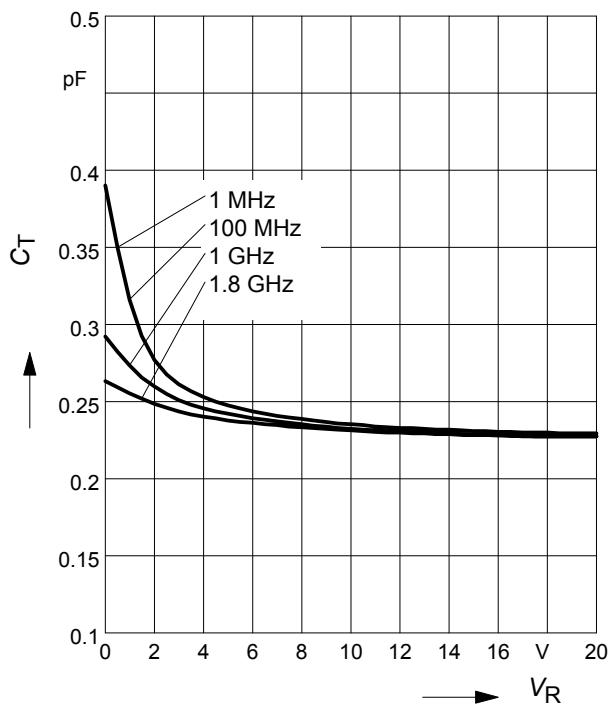
Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics					
Diode capacitance $V_R = 1 \text{ V}, f = 1 \text{ MHz}$	C_T	-	0.3	0.4	pF
$V_R = 0 \text{ V}, f = 100 \text{ MHz}$		-	0.4	-	
$V_R = 0 \text{ V}, f = 1 \text{ GHz}$		-	0.28	-	
$V_R = 0 \text{ V}, f = 1.8 \text{ GHz}$		-	0.25	-	
Reverse parallel resistance $V_R = 0 \text{ V}, f = 100 \text{ MHz}$	R_P	-	65	-	kΩ
$V_R = 0 \text{ V}, f = 1 \text{ GHz}$		-	2.5	-	
$V_R = 0 \text{ V}, f = 1.8 \text{ GHz}$		-	1.5	-	
Forward resistance $I_F = 1 \text{ mA}, f = 100 \text{ MHz}$	r_f	-	1.5	2.5	Ω
$I_F = 5 \text{ mA}, f = 100 \text{ MHz}$		-	0.8	-	
$I_F = 10 \text{ mA}, f = 100 \text{ MHz}$		-	0.6	-	
Charge carrier life time $I_F = 10 \text{ mA}, I_R = 6 \text{ mA}, \text{measured at } I_R = 3 \text{ mA}, R_L = 100 \Omega$	τ_{rr}	-	500	-	ns
I-region width	W_I	-	13	-	μm
Insertion loss ¹⁾ $I_F = 1 \text{ mA}, f = 1.8 \text{ GHz}$	I_L	-	0.11	-	dB
$I_F = 5 \text{ mA}, f = 1.8 \text{ GHz}$		-	0.07	-	
$I_F = 10 \text{ mA}, f = 1.8 \text{ GHz}$		-	0.06	-	
Isolation ¹⁾ $V_R = 0 \text{ V}, f = 0.9 \text{ GHz}$	I_{SO}	-	15	-	
$V_R = 0 \text{ V}, f = 1.8 \text{ GHz}$		-	11	-	
$V_R = 0 \text{ V}, f = 2.45 \text{ GHz}$		-	9	-	

¹BAR88-02LRH in series configuration, $Z = 50\Omega$

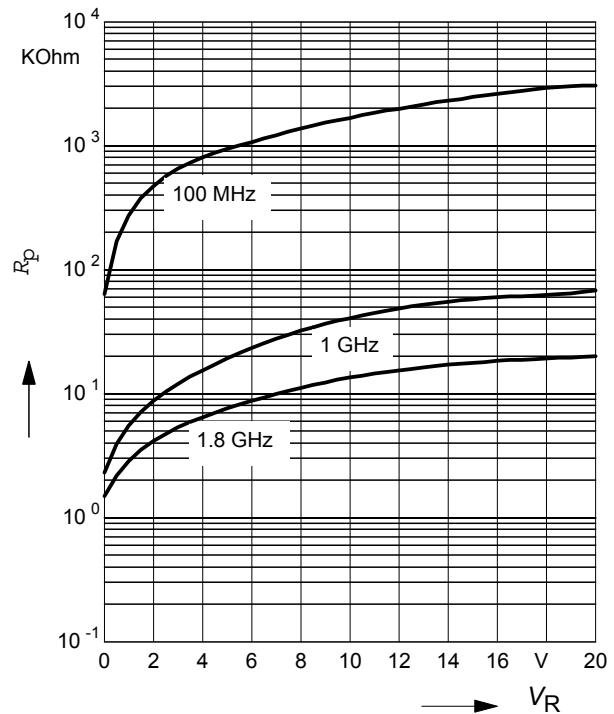
Diode capacitance $C_T = f(V_R)$

f = Parameter



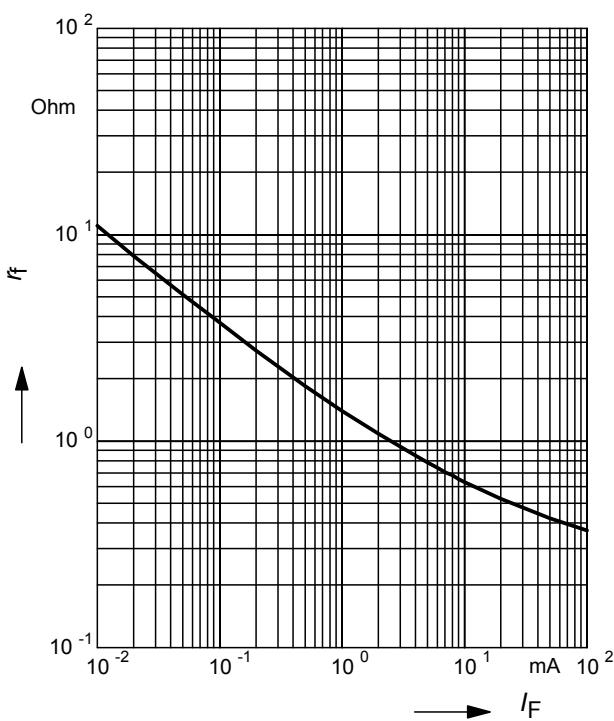
Reverse parallel resistance $R_P = f(V_R)$

f = Parameter



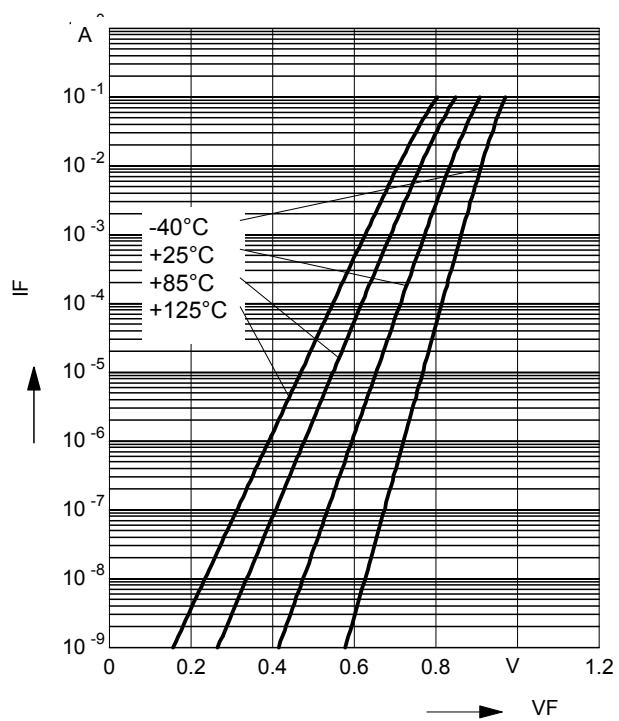
Forward resistance $r_f = f(I_F)$

f = 100MHz



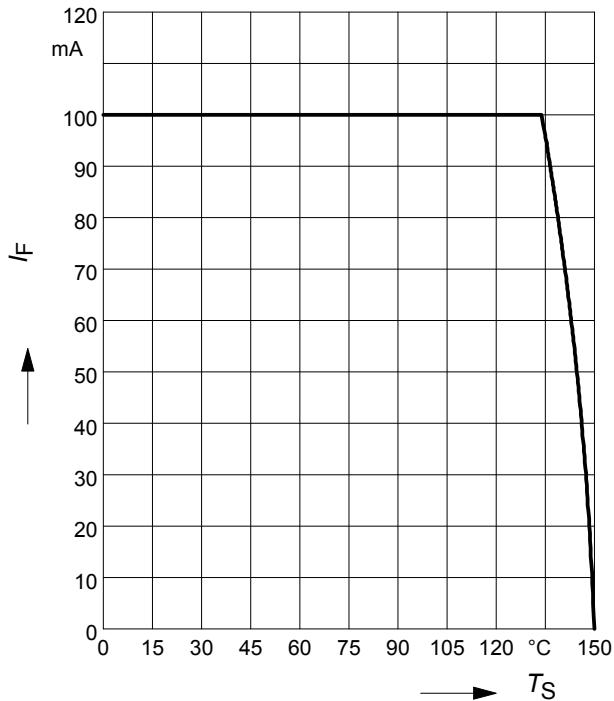
Forward current $I_F = f(V_F)$

T_A = Parameter



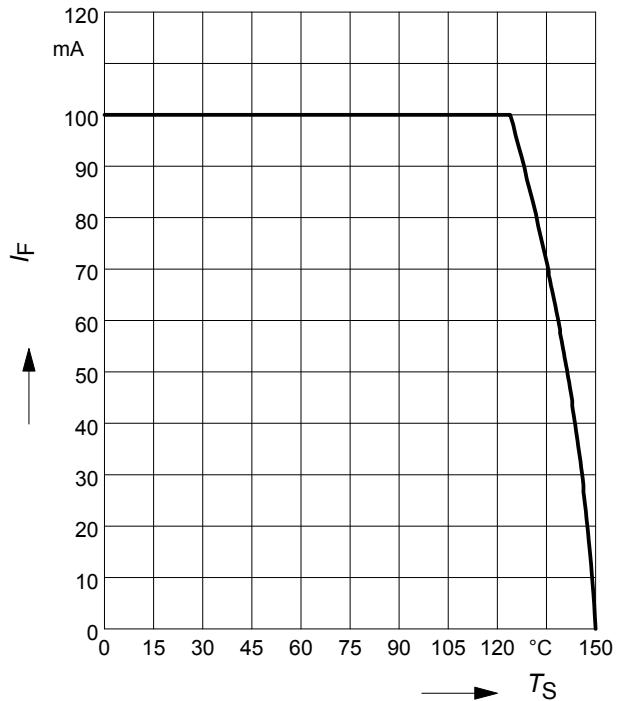
Forward current $I_F = f(T_S)$

BAR88-02LRH



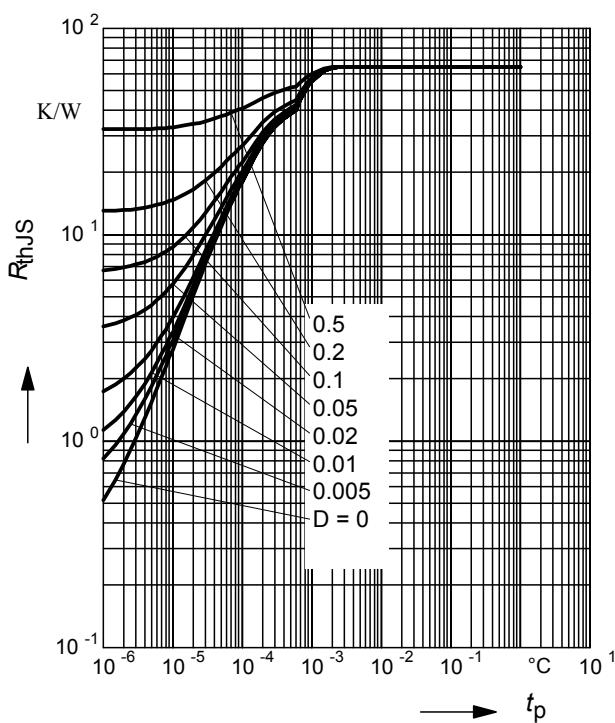
Forward current $I_F = f(T_S)$

BAR88-02V



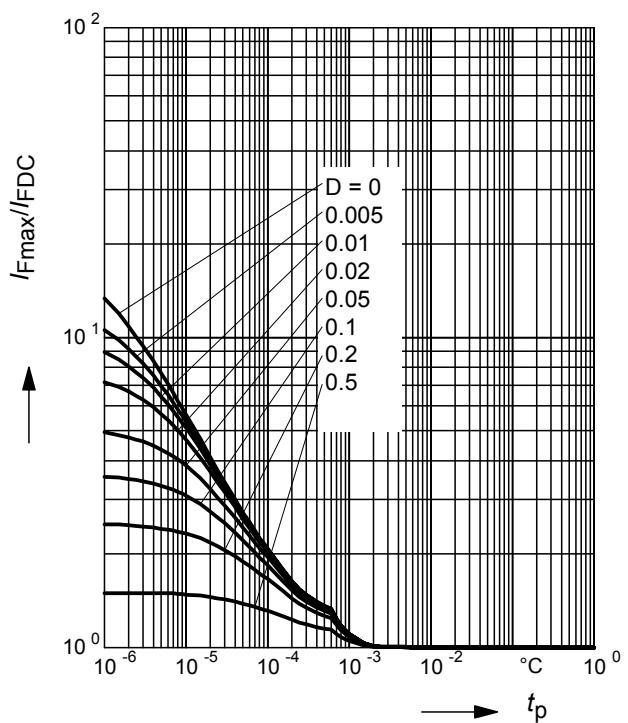
Permissible Puls Load $R_{thJS} = f(t_p)$

BAR88-02LRH



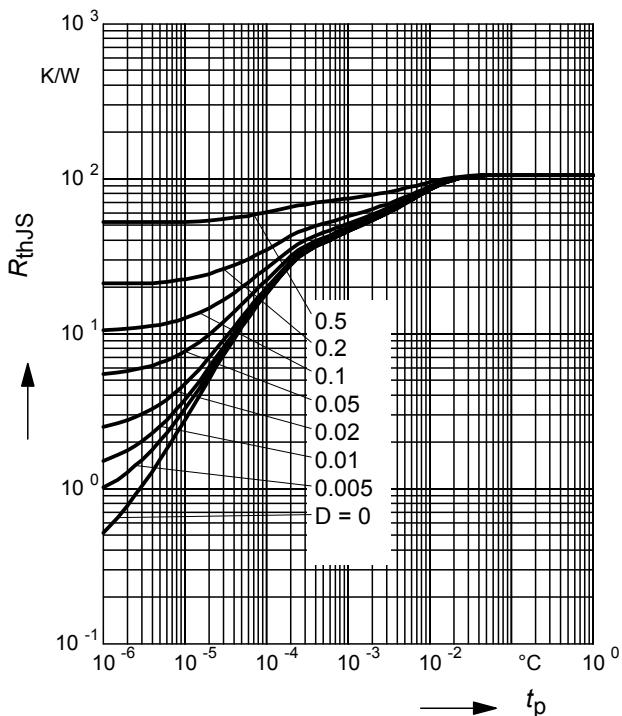
Permissible Pulse Load

$I_{Fmax}/I_{FDC} = f(t_p)$, BAR88-02LRH



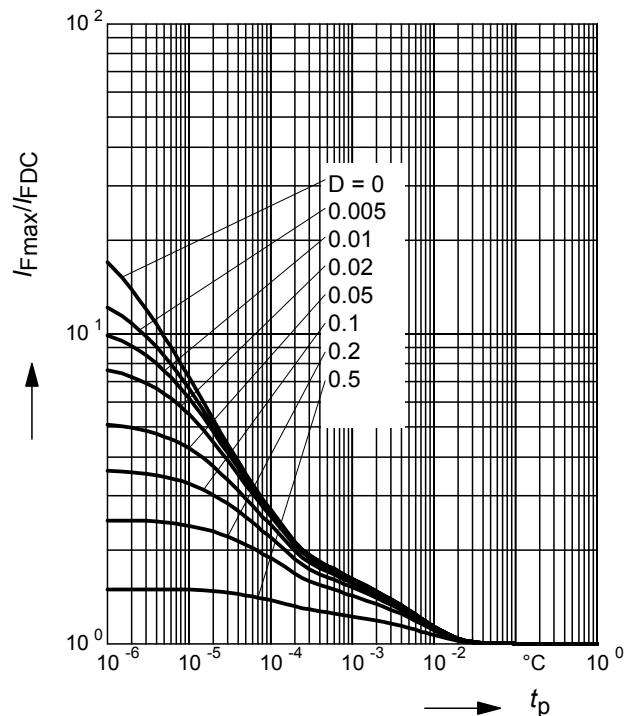
Permissible Puls Load $R_{\text{thJS}} = f(t_p)$

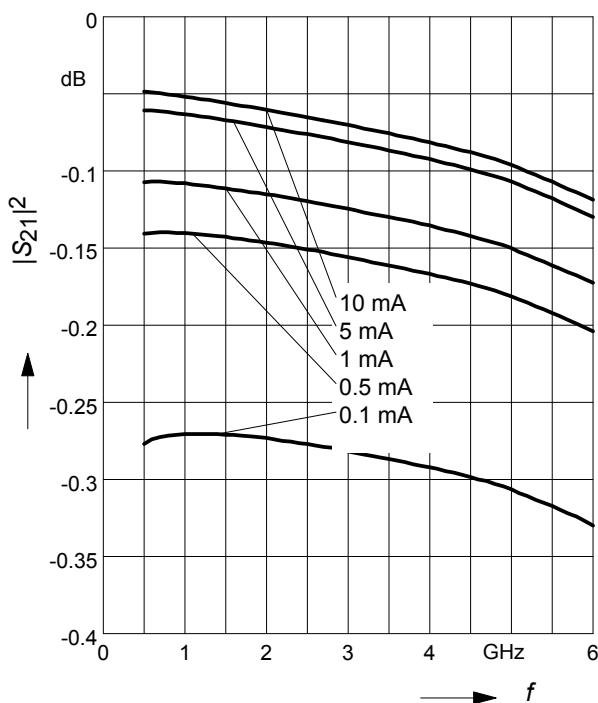
BAR88-02V

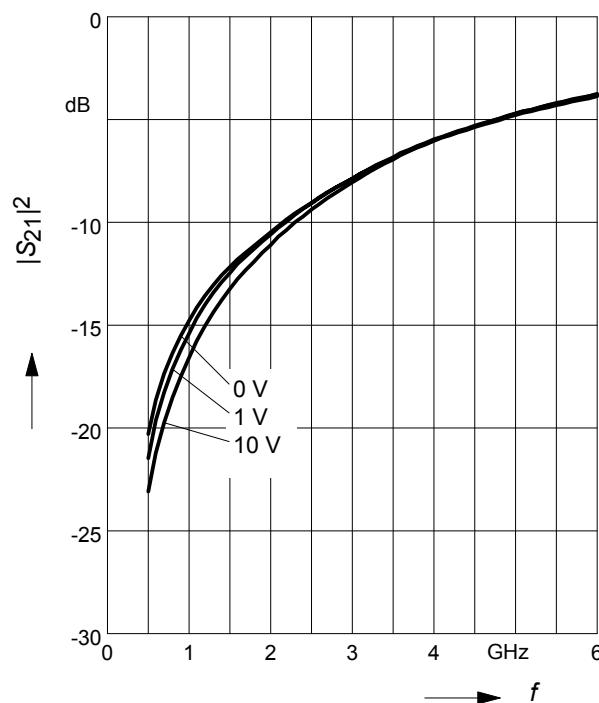

Permissible Pulse Load

$$I_{\text{Fmax}} / I_{\text{FDC}} = f(t_p)$$

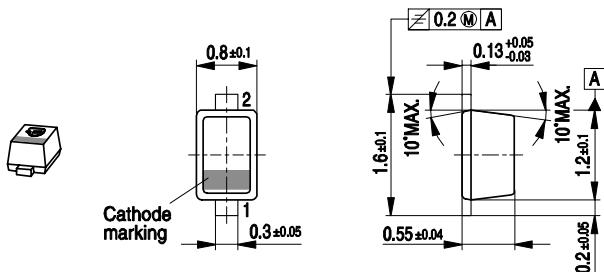
BAR88-02V


Insertion loss $I_L = -|S_{21}|^2 = f(f)$
 I_F = Parameter

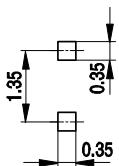
 BAR88-02LRH in series configuration, $Z = 50\Omega$

Isolation $I_{\text{SO}} = -|S_{21}|^2 = f(f)$
 V_R = Paramter

 BAR88-02LRH in series configuration, $Z = 50\Omega$


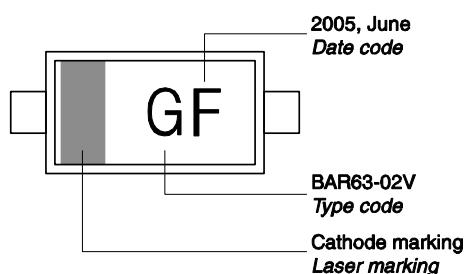
Package Outline



Foot Print

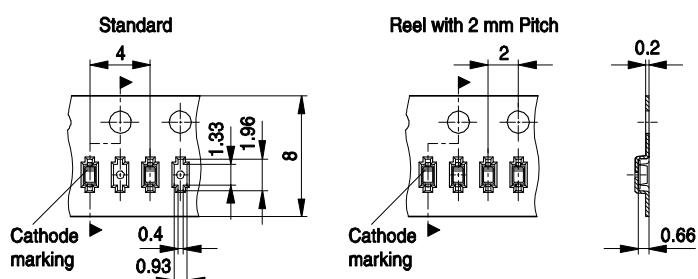


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel
 Reel ø180 mm = 8.000 Pieces/Reel (2 mm Pitch)
 Reel ø330 mm = 10.000 Pieces/Reel

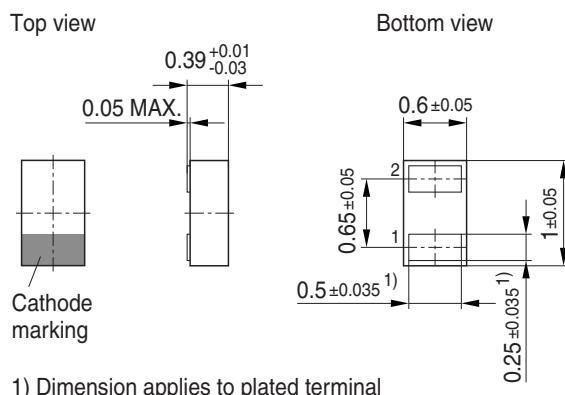


Date Code marking for discrete packages with
one digit (SCD80, SC79, SC75¹⁾) CES-Code

Month	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014
01	a	p	A	P	a	p	A	P	a	p	A	P
02	b	q	B	Q	b	q	B	Q	b	q	B	Q
03	c	r	C	R	c	r	C	R	c	r	C	R
04	d	s	D	S	d	s	D	S	d	s	D	S
05	e	t	E	T	e	t	E	T	e	t	E	T
06	f	u	F	U	f	u	F	U	f	u	F	U
07	g	v	G	V	g	v	G	V	g	v	G	V
08	h	x	H	X	h	x	H	X	h	x	H	X
09	j	y	J	Y	j	y	J	Y	j	y	J	Y
10	k	z	K	Z	k	z	K	Z	k	z	K	Z
11	l	2	L	4	l	2	L	4	l	2	L	4
12	n	3	N	5	n	3	N	5	n	3	N	5

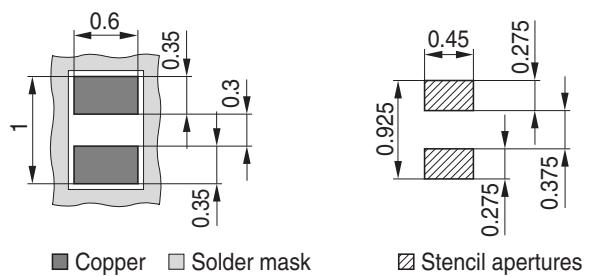
1) New Marking Layout for SC75, implemented at October 2005.

Package Outline

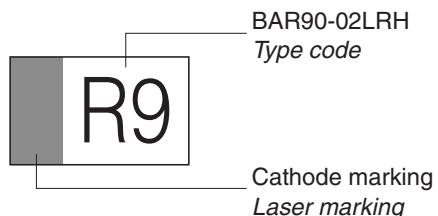


Foot Print

For board assembly information please refer to Infineon website "Packages"

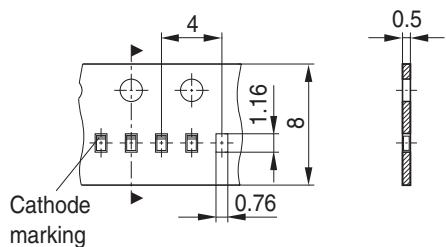


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 15.000 Pieces/Reel
Reel ø330 mm = 50.000 Pieces/Reel (optional)



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